## NSN 5961-00-883-0110

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View Online at https://aerobasegroup.com/nsn/5961-00-883-0110 **Inclosure Material:** Metal **Overall Length:** 3.327 inches Overall Diameter: 1.227 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-94 **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** 1.047 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 600.0 forward voltage, peak and 720.0 reverse voltage, instantaneous and 750.0 reverse voltage, peak and 10.0 forward gate to source voltage and 5.0 reverse gate to source voltage **Current Rating Per Characteristic:** 2.00 amperes zero-gate-voltage source current horsepower metric **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank and 0.5 watts any acceptable universal **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius case **Special Features:** One cathode lead (small wire w/lug) may be cut off if not needed. **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 insulated wire lead w/terminal lug and 1 threaded stud **Specification Data:** 80131-release4287 professional/industrial association specification Shelf Life: N/a **Unit Of Measure:** 

No

Demilitarization:

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